

STARPOWER

SEMICONDUCTOR™

IGBT

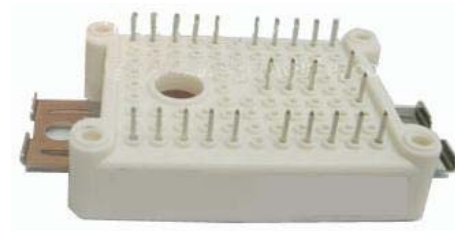
GD75HCT60L2S

Preliminary

Molding Type Module**600V/75A 4 in one-package**

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as solar power.



Features

- Low $V_{CE(sat)}$ trench IGBT technology
- Low switching losses
- 5 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Inverter for motor drive
- Solar power
- Uninterruptible power supply

IGBT $T_C=25^{\circ}\text{C}$ unless otherwise noted

Maximum Rated Values

Symbol	Description	GD75HCT60L2S	Units
V_{CES}	Collector-Emitter Voltage @ $T_j=25^{\circ}\text{C}$	600	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$ @ $T_C=80^{\circ}\text{C}$	115 75	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	150	A
P_{tot}	Total Power Dissipation @ $T_j=175^{\circ}\text{C}$	294	W
T_{SC}	Short Circuit Withstand Time	5	μs

Off Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$T_j=25^{\circ}\text{C}$	600			V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V},$ $T_j=25^{\circ}\text{C}$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V},$ $T_j=25^{\circ}\text{C}$			400	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.1\text{mA}, V_{CE}=V_{GE},$ $T_j=25^{\circ}\text{C}$	4.0		6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=75\text{A}, V_{GE}=15\text{V},$ $T_j=25^{\circ}\text{C}$		1.70	2.10	V
		$I_C=75\text{A}, V_{GE}=15\text{V},$ $T_j=175^{\circ}\text{C}$		2.10		

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=400\text{V}, I_C=75\text{A},$ $R_G=10\Omega, V_{GE}=\pm 15\text{V},$ $T_j=25^{\circ}\text{C}$		50		ns
t_r	Rise Time			70		ns
$t_{d(off)}$	Turn-Off Delay Time			200		ns
t_f	Fall Time			60		ns
E_{on}	Turn-On Switching Loss			2.5		mJ
E_{off}	Turn-Off Switching Loss			2.2		mJ
E_{tot}	Total Switching Loss			4.7		mJ

$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=400V, I_C=75A,$ $R_G=10\Omega, V_{GE}=\pm 15V,$ $T_J=175^\circ C$		55		ns
t_r	Rise Time			75		ns
$t_{d(off)}$	Turn-Off Delay Time			240		ns
t_f	Fall Time			75		ns
E_{on}	Turn-On Switching Loss			3.9		mJ
E_{off}	Turn-Off Switching Loss			2.9		mJ
E_{tot}	Total Switching Loss			6.8		mJ
C_{ies}	Input Capacitance	$V_{CE}=30V, f=1Mhz,$ $V_{GE}=0V$		4.44		pF
C_{oes}	Output Capacitance			0.25		pF
C_{res}	Reverse Transfer Capacitance			0.13		pF
I_{SC}	SC Data	$T_P \leq 5\mu s, V_{GE}=15V,$ $T_J=125^\circ C, V_{CC}=360V,$ $V_{CEM} \leq 600V$		TBD		A

DIODE $T_C=25^\circ C$ unless otherwise noted**Maximum Rated Values**

Symbol	Description	GD75HCT60L2S	Units
V_{RRM}	Collector-Emitter Voltage @ $T_J=25^\circ C$	600	V
I_F	DC Forward Current @ $T_C=80^\circ C$	75	A
I_{FRM}	Repetitive Peak Forward Current $t_p=1ms$	150	A
I^2t	I^2t -value, $V_R=0V, t_p=10ms, T_J=125^\circ C$	500	A^2s

Characteristics Values

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V _F	Diode Forward Voltage	I _F =75A,V _{GE} =0V	T _j =25℃		1.30	1.70	V
			T _j =125℃		1.35		
Q _{rr}	Recovered Charge	I _F =75A, V _R =300V, di/dt=-3600A/μs, V _{GE} =-15V	T _j =25℃		3.5		ns
			T _j =125℃		6.3		
I _{RM}	Peak Reverse Recovery Current		T _j =25℃		90		A
			T _j =125℃		100		
E _{rec}	Reverse Recovery Energy		T _j =25℃		0.80		mJ
			T _j =125℃		1.40		

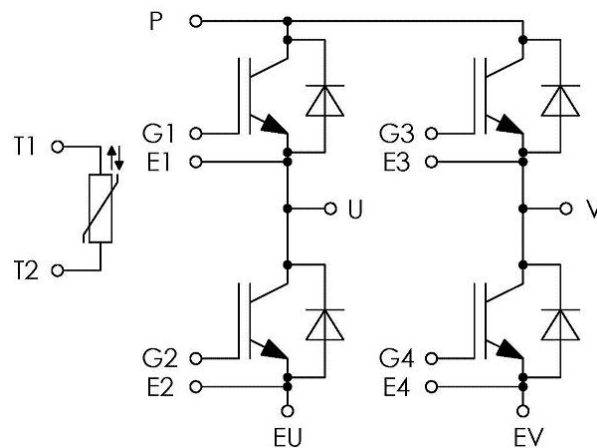
Electrical Characteristics of NTC $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
R_{25}	Rated Resistance			5.0		$\text{k}\Omega$
$\Delta R/R$	Deviation of R_{100}	$T_C=100^{\circ}\text{C}, R_{100}=493.3\Omega$	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

IGBT Module

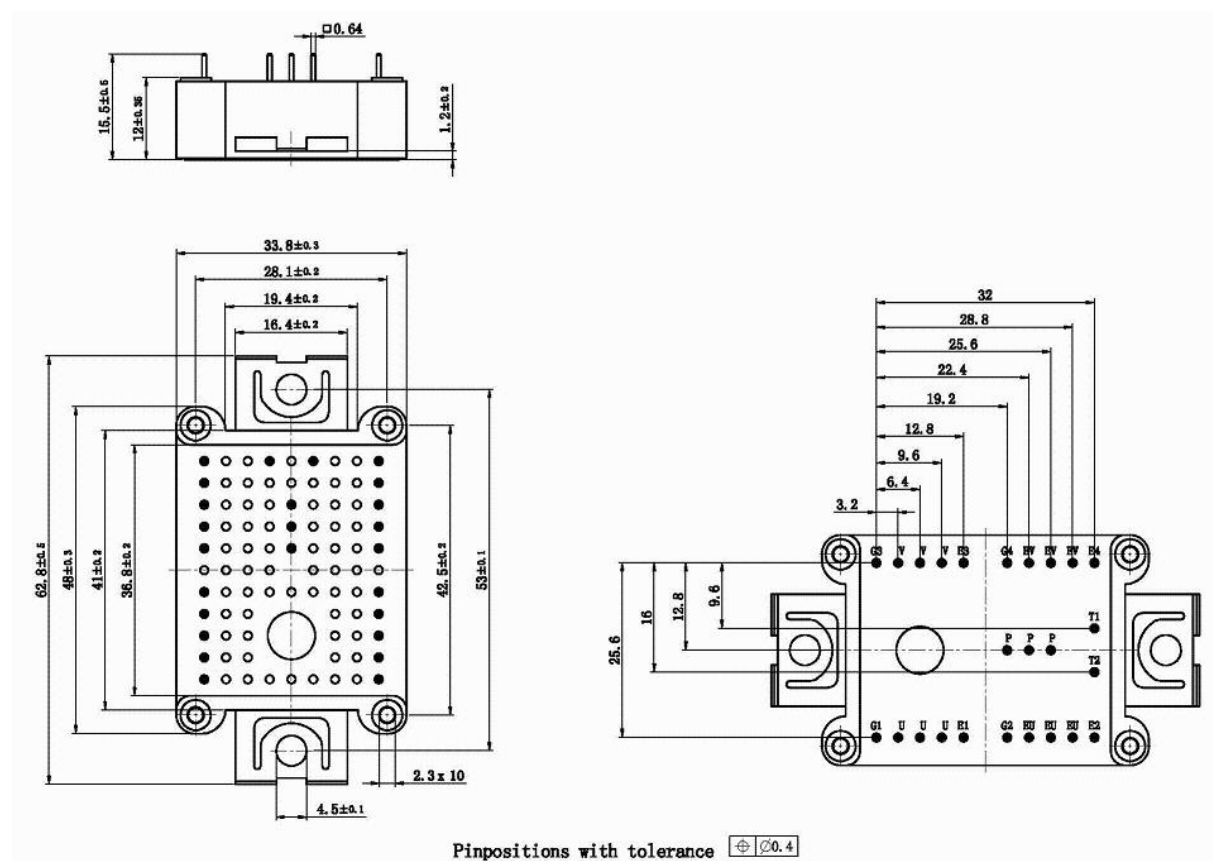
Symbol	Parameter	Min.	Typ.	Max.	Units
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$		2500		V
L_{CE}	Stray Inductance		20		nH
$R_{\text{CC}'+\text{EE}'}$	Module Lead Resistance, Terminal to Chip @ $T_C=25^{\circ}\text{C}$		8.00		$\text{m}\Omega$
$R_{\theta\text{JC}}$	Junction-to-Case (per IGBT) Junction-to-Case (per DIODE)			0.51 0.62	K/W
$R_{\theta\text{CS}}$	Case-to-Sink (Conductive grease applied)		0.08		K/W
T_j	Maximum Junction Temperature		175		$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40		125	$^{\circ}\text{C}$
F	Mounting Force Per Clamp	20		50	N
G	Weight of Module		24		g

Equivalent Circuit Schematic



Package Dimension

Dimensions in Millimeters



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